Abstracts

Application of High Power Silicon Carbide Transistors at Radar Frequencies

A.W. Morse, P.M. Esker, R.C. Clarke, C.D. Brandt, R.R. Siergiej and A.K. Agarwal. "Application of High Power Silicon Carbide Transistors at Radar Frequencies." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 677-680.

Silicon carbide (SiC) is an emerging semiconductor material which has been widely predicted to allow greatly improved transistor performance over common semiconductors such as silicon and gallium arsenide. This paper describes the characteristics of recently fabricated devices in silicon carbide, and the first application of silicon carbide transistors in high power pulsed amplifiers at radar frequencies.

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